



PSMN1R2-25YLD

N-channel 25 V, 1.2 m Ω , 230 A logic level MOSFET in LPAK56 using NextPowerS3 Technology

23 April 2021

Product data sheet

1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETS with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

2. Features and benefits

- 100% Avalanche tested at $I_{(AS)} = 169$ A
- Ultra low Q_G , Q_{GD} and Q_{OSS} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 μ A leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

3. Applications

- On-board DC:DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control
- Power OR-ing

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	25	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	[1]	-	230	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	-	172	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	1.4	1.69	m Ω

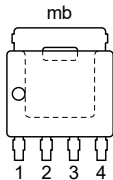
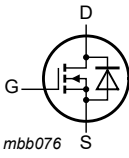
N-channel 25 V, 1.2 mΩ, 230 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	1.03	1.2	mΩ
Dynamic characteristics						
$Q_{G(\text{tot})}$	total gate charge	$I_D = 25\text{ A}$; $V_{DS} = 12\text{ V}$; $V_{GS} = 10\text{ V}$; Fig. 12 ; Fig. 13	-	60.3	-	nC
		$I_D = 25\text{ A}$; $V_{DS} = 12\text{ V}$; $V_{GS} = 4.5\text{ V}$; Fig. 12 ; Fig. 13	-	28	-	nC
		$I_D = 0\text{ A}$; $V_{DS} = 0\text{ V}$; $V_{GS} = 10\text{ V}$	-	34.4	-	nC
Q_{GD}	gate-drain charge	$I_D = 25\text{ A}$; $V_{DS} = 12\text{ V}$; $V_{GS} = 4.5\text{ V}$; Fig. 12 ; Fig. 13	-	7	-	nC
Source-drain diode						
S	softness factor	$I_S = 25\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 12\text{ V}$; Fig. 16	-	0.9	-	

[1] 230A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFPAK56; Power-SO8 (SOT669)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R2-25YLD	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R2-25YLD	1D225L

8. Limiting values

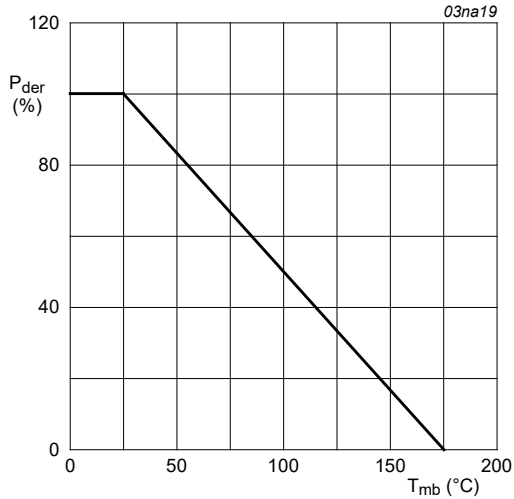
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	25	V
V _{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 k Ω		-	25	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 1		-	172	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 2	[1]	-	230	A
		V _{GS} = 10 V; T _{mb} = 100 °C; Fig. 2		-	205	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μ s; T _{mb} = 25 °C; Fig. 3		-	1163	A
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	HBM		1000	-	V
Source-drain diode						
I _S	source current	T _{mb} = 25 °C		-	143	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μ s; T _{mb} = 25 °C		-	1163	A
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 25 A; V _{sup} ≤ 25 V; R _{GS} = 50 Ω ; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; t _p = 3.18 ms		-	1293	mJ
I _{AS}	non-repetitive avalanche current	V _{sup} = 25 V; V _{GS} = 10 V; T _{j(init)} = 25 °C; R _{GS} = 50 Ω	[2]	-	169	A

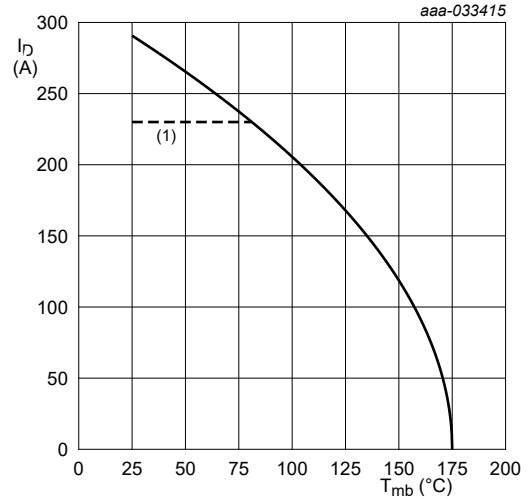
[1] 230A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

[2] Protected by 100% test



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

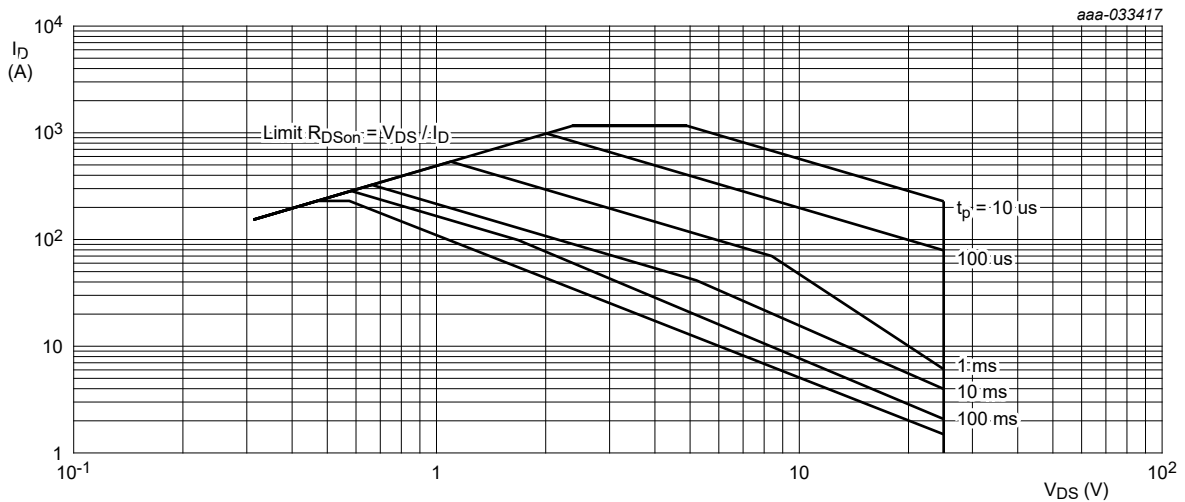
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



$V_{GS} \geq 10\text{ V}$

(1) 230A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature



$T_{mb} = 25^{\circ}\text{C}$; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	0.71	0.87	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	50	-	K/W
		Fig. 6	-	125	-	K/W

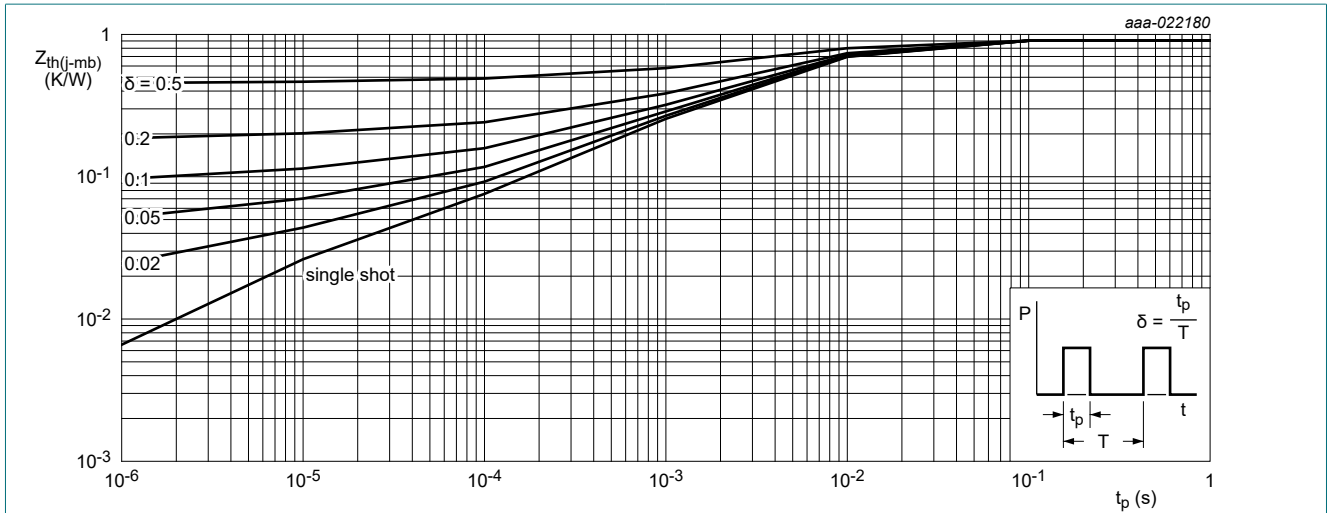
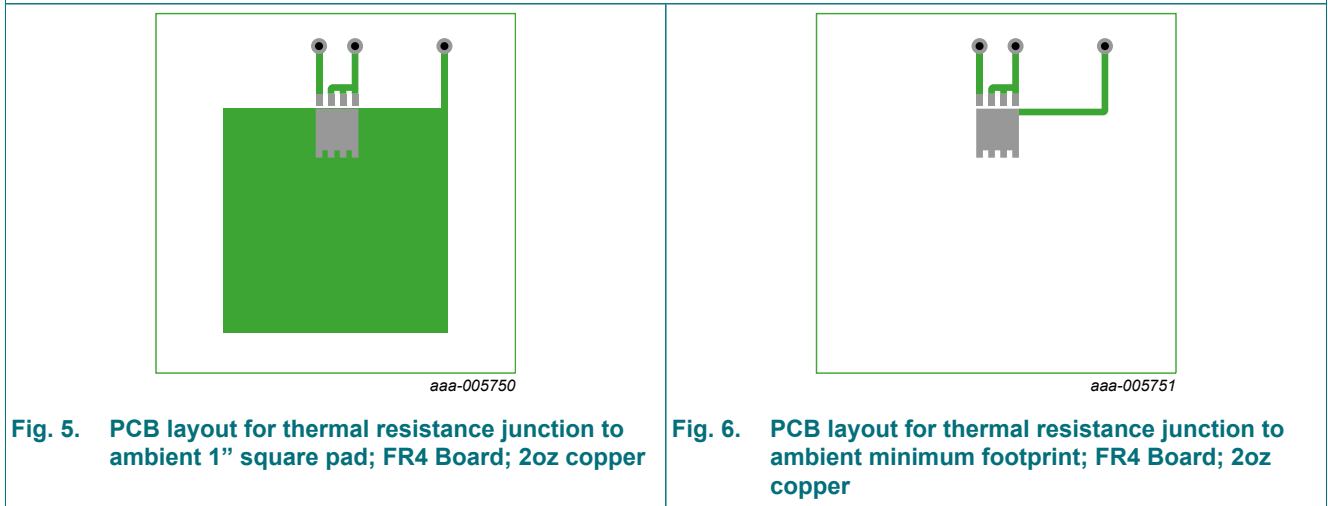


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	25	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.2	1.73	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 175 \text{ }^\circ C$	-	-4.8	-	mV/K
I_{DSS}	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	28.3	-	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	1.4	1.69	mΩ	
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 175 °C; Fig. 11	-	-	2.87	mΩ	
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	1.03	1.2	mΩ	
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11	-	-	2.01	mΩ	
R _G	gate resistance	f = 1 MHz	-	1.1	-	Ω	
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 12 V; V _{GS} = 10 V; Fig. 12 ; Fig. 13	-	60.3	-	nC	
		I _D = 25 A; V _{DS} = 12 V; V _{GS} = 4.5 V; Fig. 12 ; Fig. 13	-	28	-	nC	
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	34.4	-	nC	
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 12 V; V _{GS} = 4.5 V; Fig. 12 ; Fig. 13	-	10.4	-	nC	
Q _{GS(th)}	pre-threshold gate-source charge		-	6.4	-	nC	
Q _{GS(th-pl)}	post-threshold gate-source charge		-	4	-	nC	
Q _{GD}	gate-drain charge		-	7	-	nC	
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 12 V; Fig. 12 ; Fig. 13	-	2.7	-	V	
C _{iss}	input capacitance	V _{DS} = 12 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 14	-	4327	-	pF	
C _{oss}	output capacitance		-	1734	-	pF	
C _{rss}	reverse transfer capacitance		-	292	-	pF	
t _{d(on)}	turn-on delay time	V _{DS} = 12 V; R _L = 0.6 Ω; V _{GS} = 4.5 V; R _{G(ext)} = 5 Ω	-	25.1	-	ns	
t _r	rise time		-	30.3	-	ns	
t _{d(off)}	turn-off delay time		-	28.9	-	ns	
t _f	fall time		-	20.2	-	ns	
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 12 V; f = 1 MHz; T _j = 25 °C	-	31.2	-	nC	
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 15	-	0.8	1.2	V	
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 12 V; Fig. 16	-	33.5	-	ns	
Q _r	recovered charge		[1]	-	29.7	-	nC
t _a	reverse recovery rise time		-	-	17.4	-	ns
t _b	reverse recovery fall time		-	-	16.1	-	ns
S	softness factor		-	-	0.9	-	

[1] includes capacitive recovery

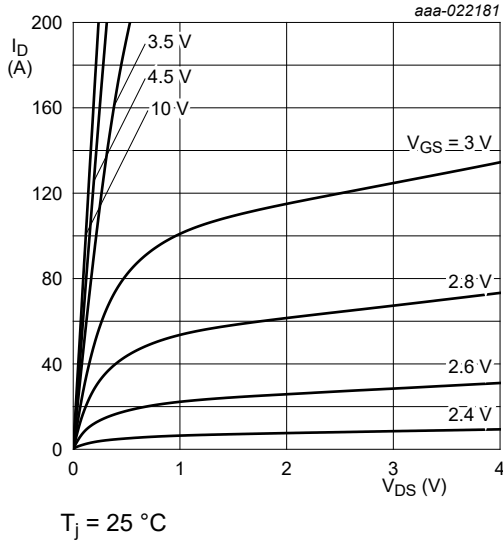


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

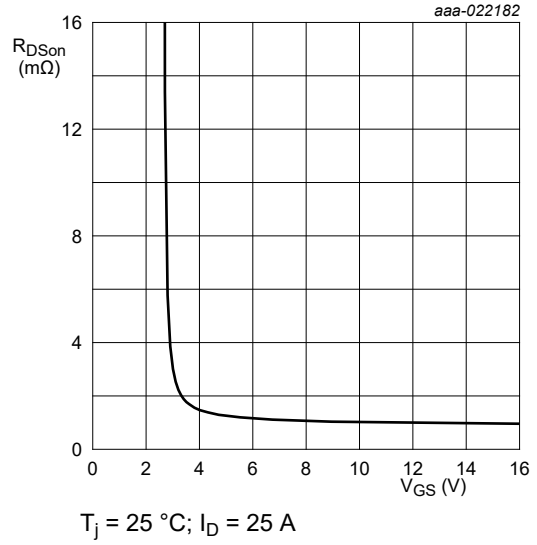


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

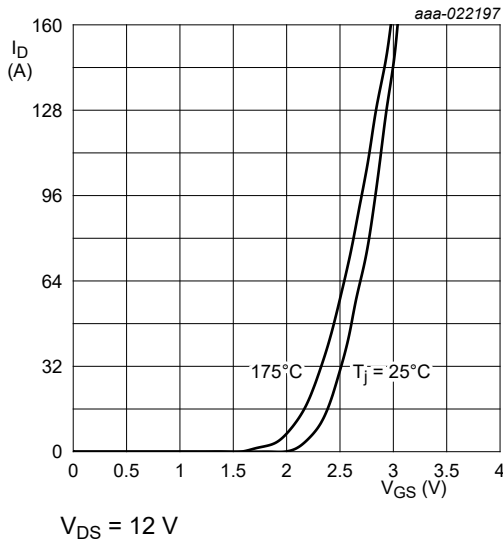


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

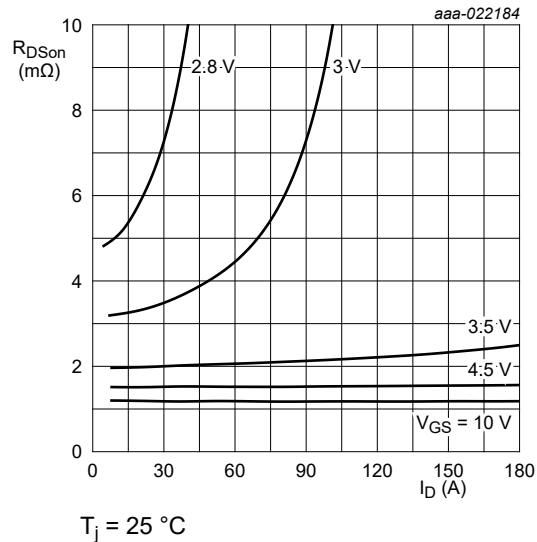
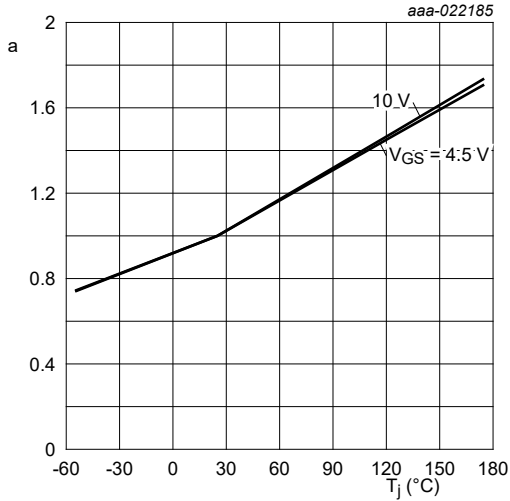


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

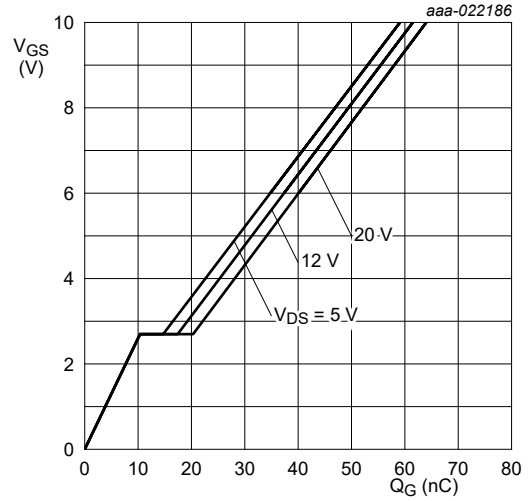


Fig. 12. Gate-source voltage as a function of gate charge; typical values

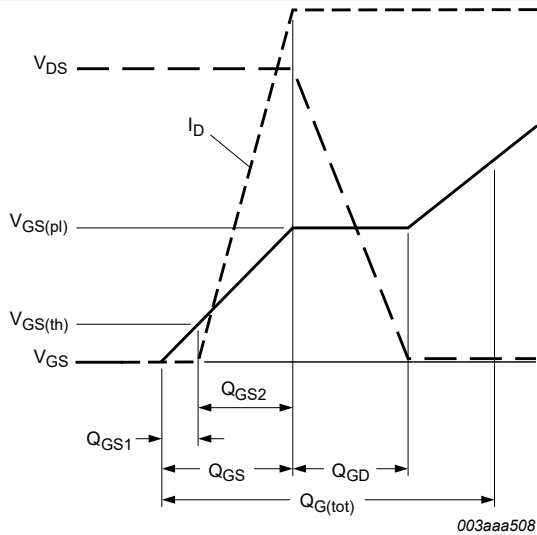


Fig. 13. Gate charge waveform definitions

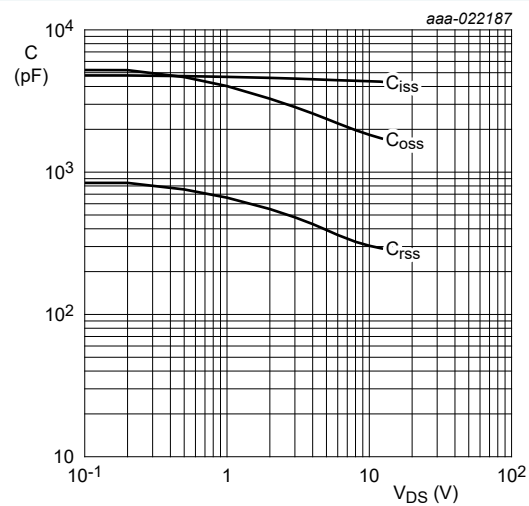
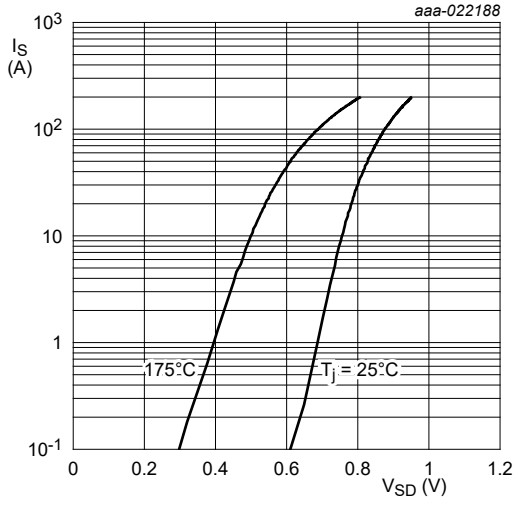


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

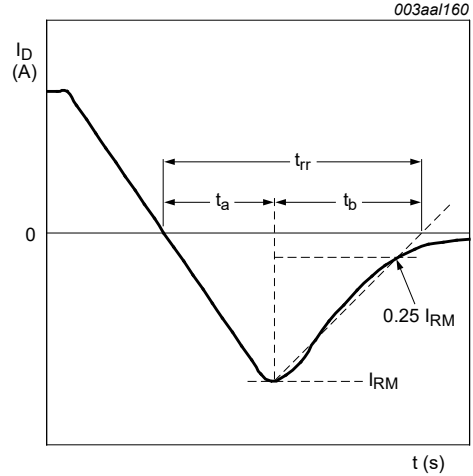


Fig. 16. Reverse recovery timing definition

11. Package outline

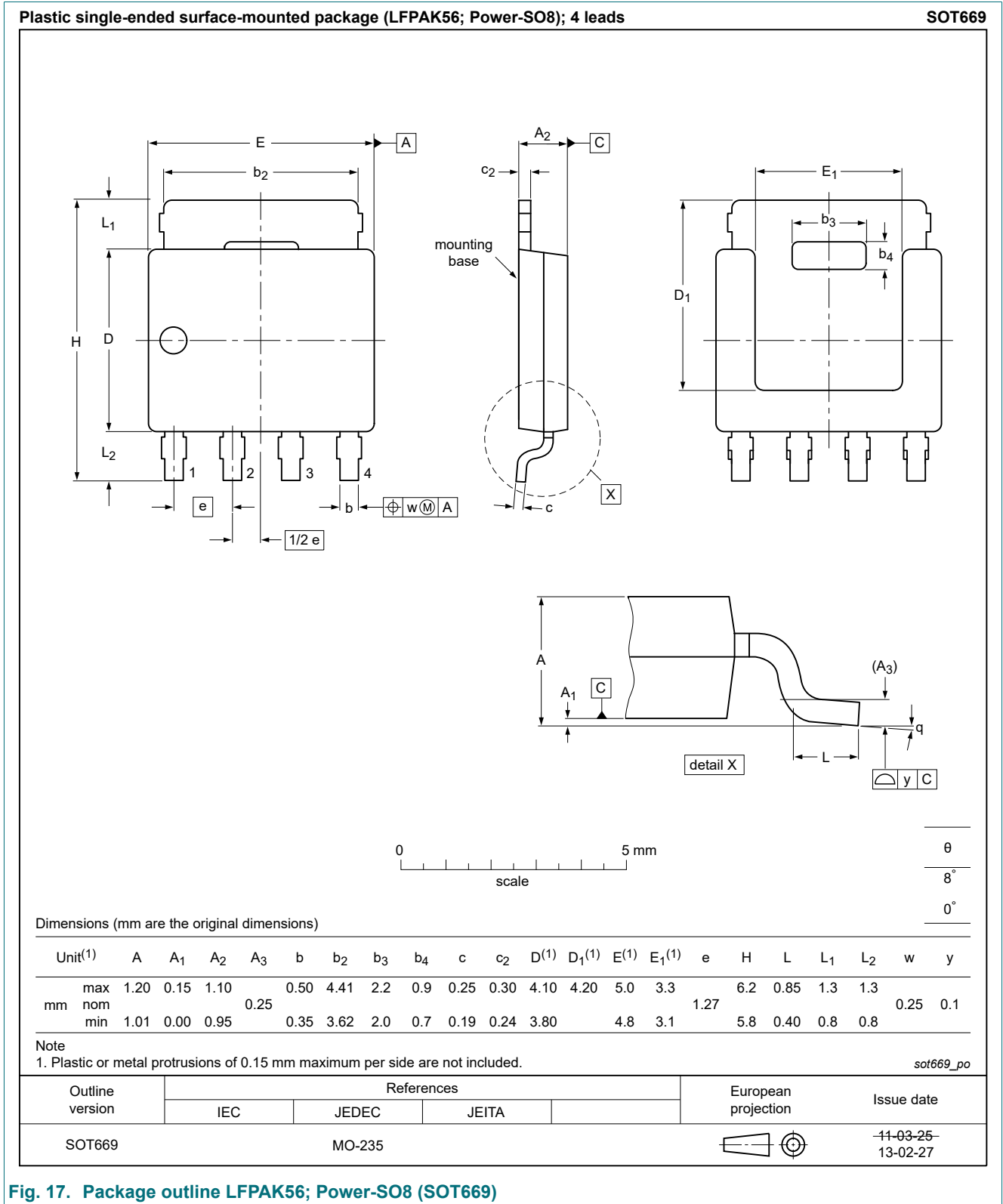


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

12. Soldering

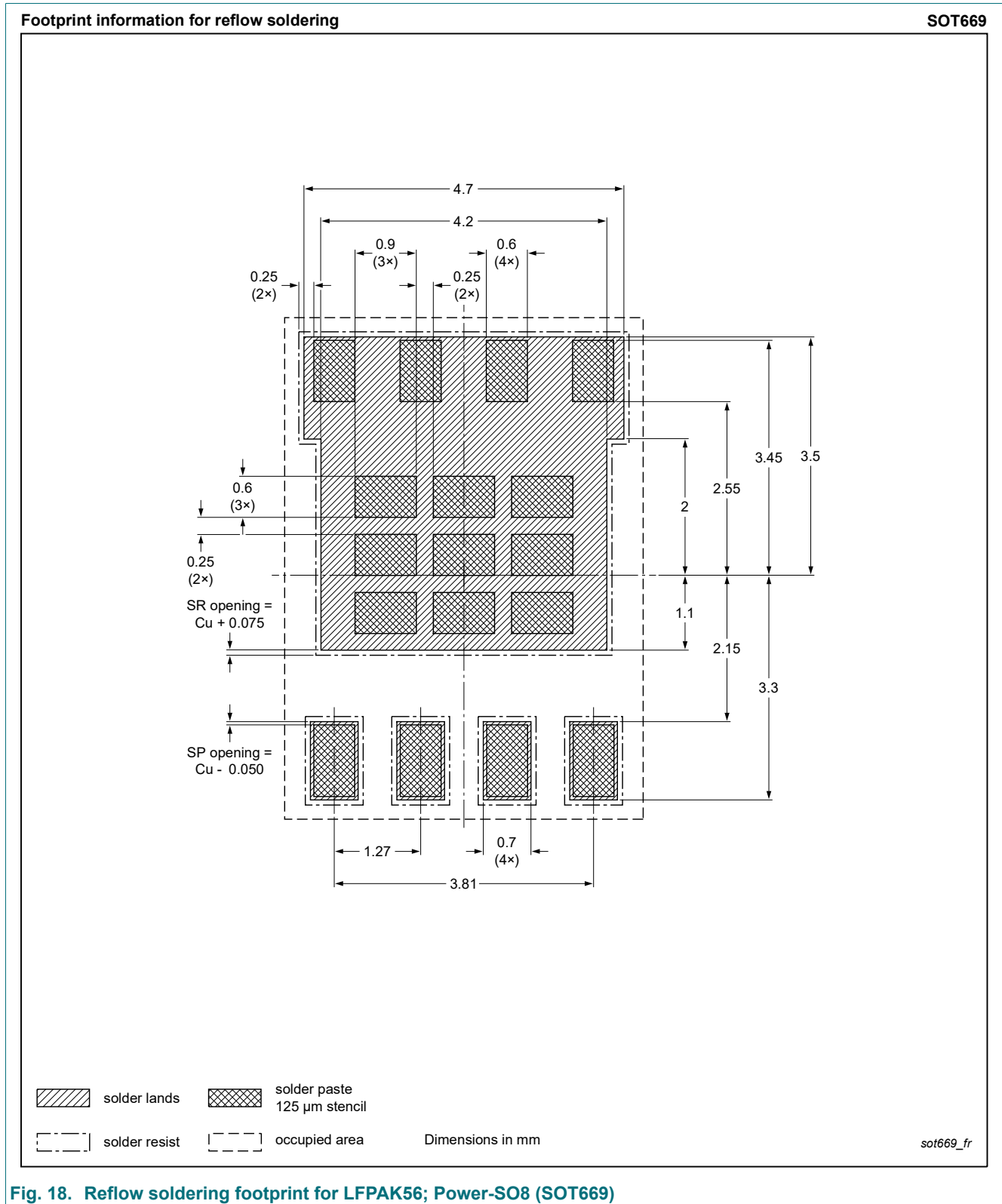
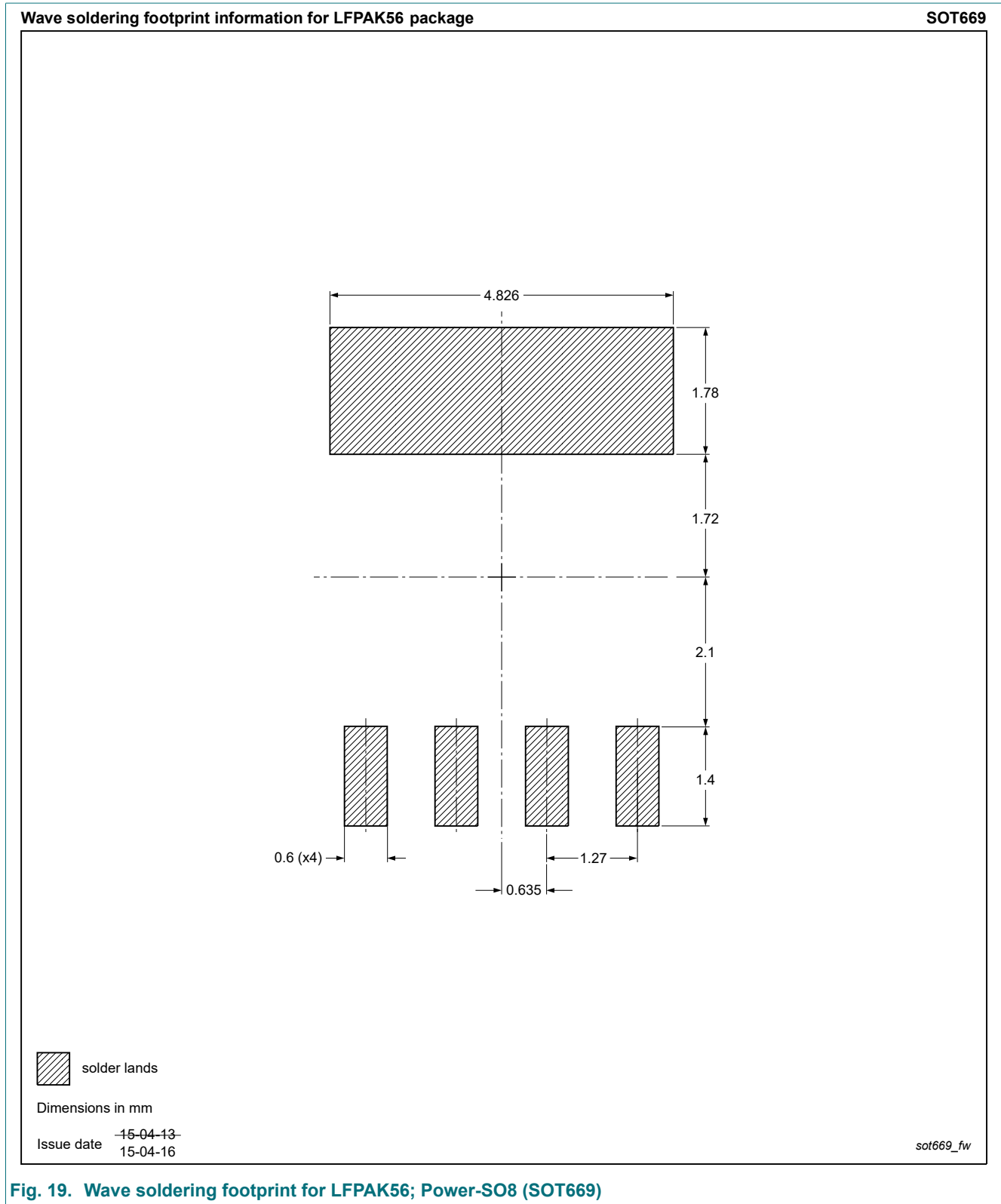


Fig. 18. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Date of release: 23 April 2021
